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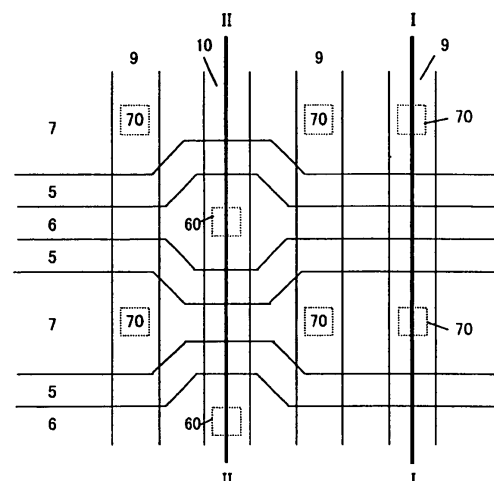
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(54) **SEMICONDUCTOR STORAGE DEVICE AND ITS MANUFACTURING METHOD**

(57) A drain (7) comprises a lightly-doped shallow impurity region (7a) aligned with a control gate (5), and a heavily-doped deep impurity region (7b) aligned with a sidewall film (8) and doped with impurities at a concentration higher than that of the lightly-doped shallow impurity region (7a). The lightly-doped shallow impurity region (7a) leads to improvement of the short-channel effect and programming efficiency. A drain contact hole forming portion (70) is provided to the heavily-doped impurity region (7b) to reduce the contact resistance at the drain (7).

FIG. 1A



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FIG. 1B

<SECTION I-I>

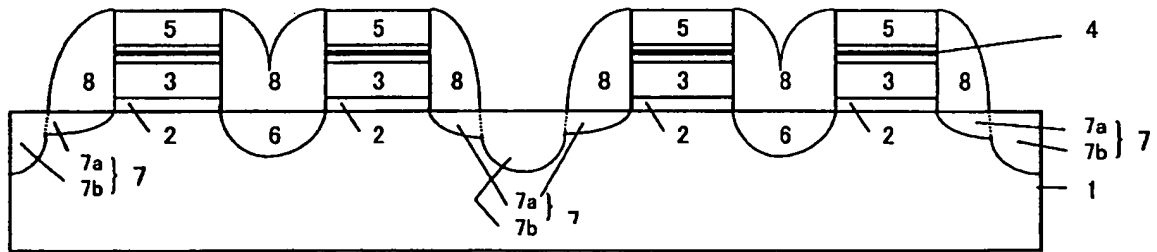


FIG. 1C

<SECTION II-II>

